



TO-126 Plastic-Encapsulate Transistors

2SB1658 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

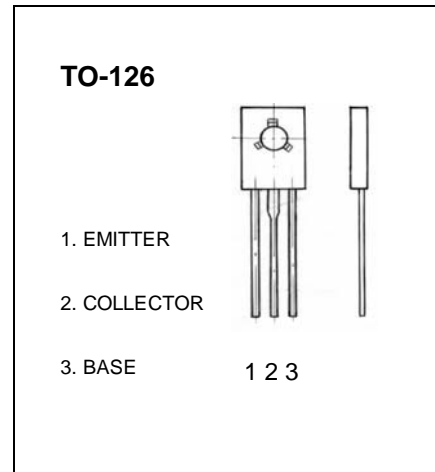
I_{CM} : -5 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-1A$	150		600	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-4A$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1A, I_B=-50mA$ $I_C=-2A, I_B=-100mA$ $I_C=-4A, I_B=-200mA$			-0.15 -0.25 -0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-1A, I_B=-100mA$			-1.5	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA$		95		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		100		pF